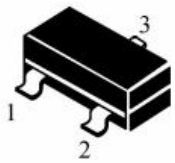
安徽富信半导体科技有限公司

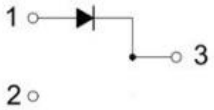
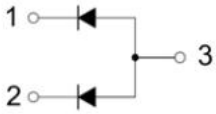
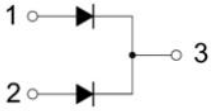
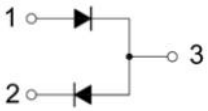
ANHUI FOSAN SEMICONDUCTOR TECHNOLOGY CO. , LTD.

BAT54W/AW/CW/SW



SOT-323 Schottky Barrier Diode 肖特基势垒二极管

■ Internal Configuration& Device Marking 内部结构与产品打标

Type 型号	BAT54W	BAT54AW	BAT54CW	BAT54SW
Pin 管脚				
Mark 打标	KL5/L4	KL6/L42	KL7/L43	KL8/L44

■Absolute Maximum Ratings 最大额定值

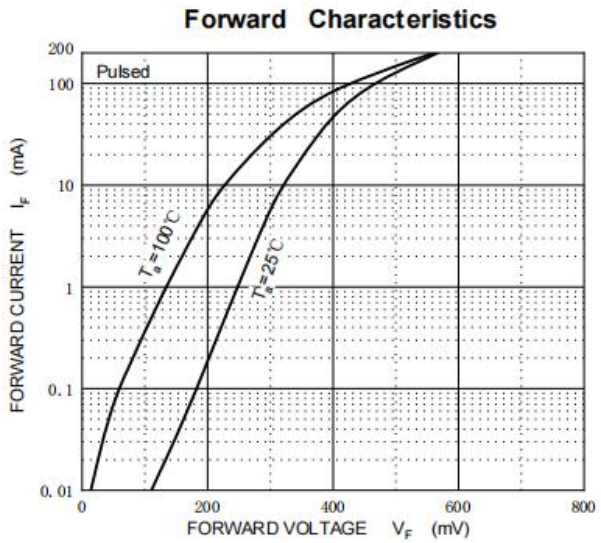
Characteristic 特性参数	Symbol 符号	Rat 额定值	Unit 单位
Peak Reverse Voltage 反向峰值电压	V_{RRM}	30	V
Reverse Work Voltage 反向工作电压	V_{RWM}		
DC Reverse Voltage 直流反向电压	V_R		
Forward Work Current 正向工作电流	$I_F(I_O)$	200	mA
Repetitive Peak Forward Current 重复峰值正向电	I_{FRM}	300	mA
Peak Surge Forward Current 峰值浪涌正向电流	I_{FSM}	600	mA
Power dissipation 耗散功率	P_D(Ta=25℃)	200	mW
Thermal Resistance J-A 结到环境热阻	$R_{\theta JA}$	500	℃/W
Junction and Storage Temperature 结温和储藏温度	T_J,T_{stg}	125,-55to+150℃	

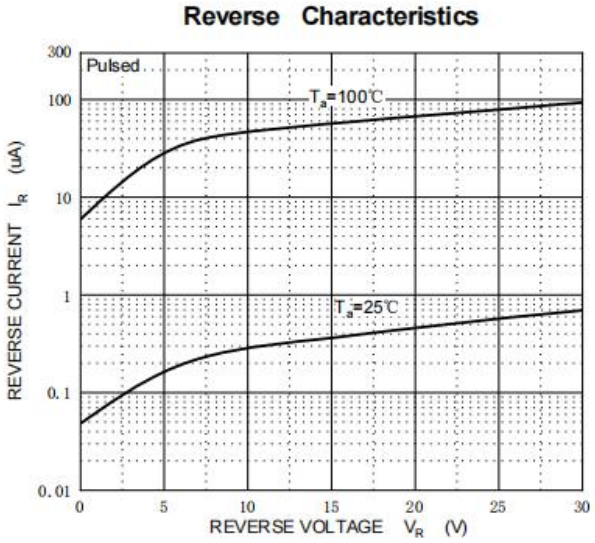
■Electrical Characteristics 电特性

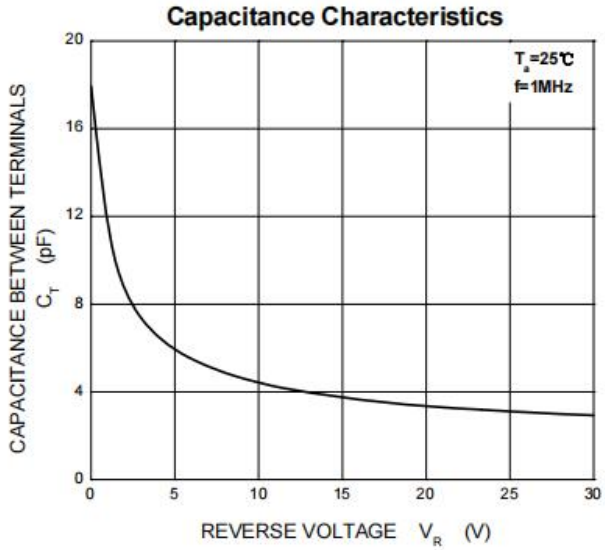
(T_A=25℃ unless otherwise noted 如无特殊说明，温度为 25℃**)**

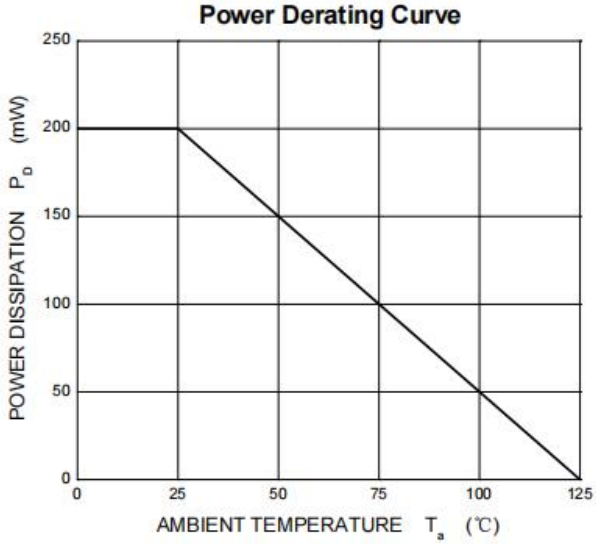
Characteristic 特性参数	Symbol 符号	Min 最小值	Max 最大值	Unit 单位
Reverse Breakdown Voltage 反向击穿电压(I_R=100μA)	$V_{(BR)}$	30	—	V
Reverse Leakage Current 反向漏电流(V_R=25V)	I_R	—	2	μA
Forward Voltage(I_F=0.1mA) 正向电压(I_F=1mA) (I_F=10mA) (I_F=30mA) (I_F=100mA)	V_F	—	0.24 0.32 0.4 0.5 1	V
Diode Capacitance 二极管电容(V_R=1V, f=1MHz)	C_D	—	10	pF
Reverse Recovery Time 反向恢复时间	T_{rr}	—	5	nS

■Typical Characteristic Curve 典型特性曲线

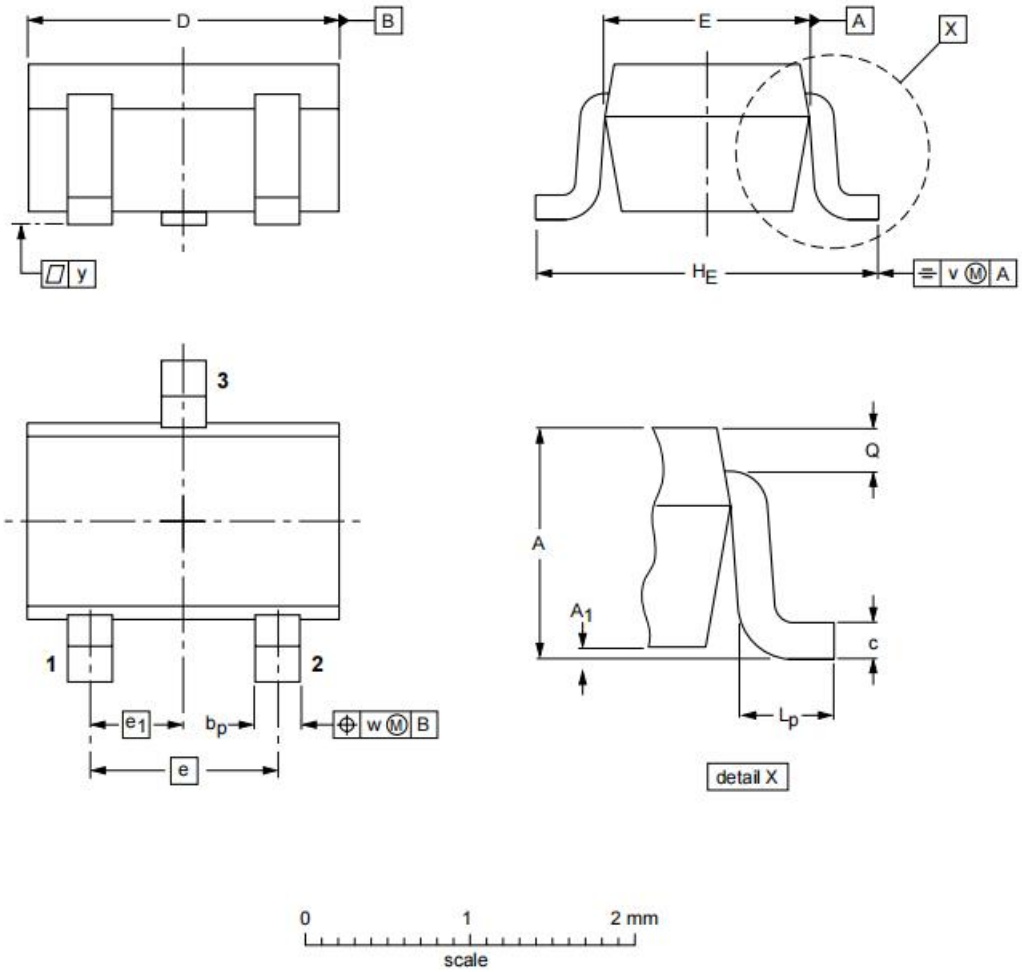








■**Dimension** 外形封装尺寸



DIMENSIONS (mm are the original dimensions)

UNIT	A	A_1 max	b_p	c	D	E	e	e_1	H_E	L_p	Q	v	w
mm	1.1 0.8	0.1	0.4 0.3	0.25 0.10	2.2 1.8	1.35 1.15	1.3	0.65	2.2 2.0	0.45 0.15	0.23 0.13	0.2	0.2